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# **Computational Study of Structural and Electronic Properties of Undoped SnO<sub>2</sub> for Renewable Energy**

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**Abstract.** Throughout this research, we report on ab-initio study of structural and electronic properties of undoped  $SnO_2$  in rutile phases using the full-potential linearized-augmented-plane waves method (DFT/FP-LAPW) within the local density (LDA) and TB-mBJ (Tran–Blaha modified Becke–Johnson) correction of gap energy and total density of states. The calculated equilibrium lattice parameters are used for plotting the density of states (DOS) and band structure diagrams. The computational results, which we have found, are compared to author's experimental and theoretical measurements.

*Keywords*. SnO<sub>2</sub>, DFT/FP-LAPW, TB-mBJ, LDA; Renewable energy.

# **INTRODUCTION**

Tin oxide (SnO<sub>2</sub>) is transparent conductive oxides, it is n-type semiconductor with a large band gap ( $E_g = 3.5 \text{ eV}$ ), is a material with important technological applications. It used widely as a component in microelectronic (Fabrício Sensato et al., 2002) and thermoelectric applications (Borges et al., 2015) like gas sensors, solar cell (Agashe et al., 2008) and catalyst (Kolmakov et al., 2003). It was one of the first oxides studied and the most frequently used in high sensibility gas sensors by electrical conductivity variations (Göpel and Schierbaum, 1995). SnO<sub>2</sub> is generally noted as a nonstoichiometric oxide, because of deficiently of oxygen. The sensibility to oxygen comes from to the variable valency of Sn. The presence of oxygen that is in the forms of radical ion in different charged states leads to reduce a part of Sn<sup>4+</sup> to Sn<sup>2+</sup>. Because of its critical importance in device fabrication and performance, the SnO<sub>2</sub> attract great attention of many researchers in recent years and there are variety works have been reported concerning doped and undoped SnO<sub>2</sub> using theoretical or experimental study. In this article, we investigate the structural and electronic properties of the rutile phase of SnO<sub>2</sub>. First, we calculate the structural properties, after that we calculate the electronic (band energy) properties. Then, we discuss the obtained results.

The ab initio calculations described here are performed with the Wien2k code under Linux based on density functional theory (DFT\_FP-LAPW). We use local density approximation LDA and the modified TB-mBJ (Tran-Blaha modified Becke-Johnson) (Schleife et al., 2011; Koller et al., 2011) who is more efficient to predict the electronic properties than LDA. Throughout this research, LDA approximation with TB-mBj correction is used for undoped SnO<sub>2</sub> material. Up to our knowledge, only GGA approximation with TB-mBj correction is used (Hammi et al., 2016), LDA method has not been used before and no paper is previously reported.

## **COMPUTATIONAL DETAILS**

In this study, we have used the density functional theory (DFT) with the method of fullpotential linearized augmented plane-wave (FP-LAPW). This method is implemented in WIEN2K package (Blaha et al., 2001; Madsen et al., 2001). We have been used to study all properties (structural, electronic and optic) by local density approximation LDA, it's based on the parameterization given by Moruzzi et al. (1978), the LDA approximation is the most widely used approximation, in density functional theory because she gives the goods results. We have also used the modified TB-mBJ (Tran-Blaha modified Becke-Johnson) exchange potential for LDA (Becke and Johnson, 2006), which greatly improves band gap calculation; it has been integrated with the Wien2K package.

Tin oxide SnO<sub>2</sub> crystallizes in rutile form with space group P<sub>42/mnm</sub>, the Wyckoff of Tin (Sn) atoms at position (0, 0, 0) and  $(\frac{1}{2}, \frac{1}{2}, \frac{1}{2})$  and four Oxygen (O) atoms at position  $\pm$  (u, u, 0;  $\frac{1}{2}+u$ ,  $\frac{1}{2}-u$ ,  $\frac{1}{2}$ ) in each primitive cell. In this work the optimized lattice parameters for SnO<sub>2</sub> unit cell are (a = b = 4.74, c=3.19) and ( $\alpha = \beta = \gamma = 90^{\circ}$ ) with ideal u= 0.306, the radi of the muffin tin atomic spheres R<sub>MT</sub> of Sn and O atoms have been 1.95 and 1.68 Bohr, respectively.  $R_{MT} \times K_{MAX}$  (cutoff parameter) have been set to 7.0 where  $R_{MT}$  de notes the smallest muffin tin radius of atoms and K<sub>MAX</sub> is the maximum value of the reciprocal lattice vectors used in the plane wave expansion, the Brillouin-zone integration for geometry optimizations and electronic property calculations was performed by using a 3000 k-point.

## **RESULTS AND DISCUSSION**

## **Structural properties:**

The rutile-type SnO<sub>2</sub> belongs to space group P<sub>42/mnm</sub> (Fig.1). It is characterized by two lattice parameters **a**, **c** and the internal parameter **u**. it's unit cell contains two tin atoms are set at (0, 0, 0;  $\frac{1}{2}$ ,  $\frac{1}{2}$ ,  $\frac{1}{2}$ ) and four oxygen atoms in the following positions  $\pm$  (u, u, 0; u +  $\frac{1}{2}$ ,  $\frac{1}{2}$ -u,  $\frac{1}{2}$ ). We notice that the oxygen atomic positions depend on the internal parameter **u**. To find the atomic positions of equilibrium, the parameters can be optimized by calculating the forces on the nuclei and using the damped Newton scheme (Kohler et al., 1996). The total energies were then calculated as a function of volume (Fig. 2 (a)) and the obtained data fitted to the Murnaghan equation of state (Murnaghan, 1944):

$$E(V) = \frac{B_0 V}{B_0'} \left[ \frac{\left(\frac{V_0}{V}\right)^{B_0'}}{B_0' - 1} + 1 \right] + E_0 - \frac{V_0 B_0}{B_0' - 1}$$
(1)  
Where:

$$B_0 = V \frac{d^2 E}{dV^2} \tag{2}$$

In figure 2 (b) The c/a ratio has also been optimized at a constant volume. Our results showed that the most stable structure of rutile-type  $SnO_2$  occurs when the axial ratio c/a = 0.679 and u a = 0.306. The structural parameters, bulk properties obtained by using LDA are listed in table 1.

We notice that the obtained results are more compatible with the other calculations and experimental value. Our results are compared with other theoretical calculations and experimental results.

The value of lattice constant a is 1% lower than lattice constant an of experiments value but lattice constant c is 1-2% greater than lattice constant c of experiments value, we found that the most stable structure of rutile-type  $SnO_2$  occurs at c/a=0.6797 in our calculus. About bulk modulus  $B_0$  and pressure derivative $B'_0$ , our value are 2-4% lower than experiments values.



Fig. 1. The optimized structure of pure rutile-SnO<sub>2</sub>.



(a) volume (b) ratio c/a for primitive cell of pure rutile-SnO<sub>2</sub> Fig. 2. Calculated total energies as a function, respectively calculated within the DFT-LDA.

	Present work DFT- LDA	Other theo.	Exp.
а	4.71985	4.830 - 4.776 - 4.826 - 4.715 (Erdem et al., 2014 ; Hassan et al., 2013 ; Duan, 2008 ; Gracia et al., 2007)	4.737 (Haines and Léger, 1997)
с	3.2081	3.236 - 3.212 - 3.237- 3.194 (Erdem et al., 2014 ; Hassan et al., 2013 ; Duan, 2008 ; Gracia et al., 2007)	3.186 (Haines and Léger, 1997)
c/a	0.6797	-	-
u	0.306	0.306 - 0.307 (Erdem et al., 2014 ; Hassan et al., 2013 ; Duan, 2008 ; Gracia et al., 2007)	0.307 (Haines and Léger, 1997)
$\mathbf{B}_0$	218.96	173 – 192 - 179 - 228 (Erdem et al., 2014; Hassan et al., 2013; Duan, 2008; Gracia et al.,	205 (Haines and Léger, 1997)

Table 1. DFT calculations of equilibrium structural parameters of a (Å), c (Å), internal parameter u, ratio c/a, bulk modulus at zero pressure  $B_0$  (GPa), its pressure derivative  $B'_0$  and volume  $V_0$  (Bohr).

4		2007)			
B,	4.9047	5.4 - 4.8 - 5 - 4 (Erdem et al., 2014; Hassan et	7 (Haine	s and	Léger,
		al., 2013; Duan, 2008; Gracia et al., 2007)	1997)		-
$V_0$	482.2803	-	-		

#### **Electronic properties**

Figure 3 shows the calculated band structure and the projected density of states (DOS) for rutile-phase of SnO<sub>2</sub> as obtained by including the modified Becke-Johnson exchange potential (LDA-TB-mBJ) along the A-M-X- $\Gamma$ -R-Z-A path in the first Brillouin zone, the Fermi level is referred to be zero. We notice that rutile SnO<sub>2</sub> has direct band gap at  $\Gamma$  point, the value of calculated band gap obtained by the difference between the valence band maximum and the minimum of conduction band. At figure 4 we drew the total density of state (TDOS) and the partial density of state (PDOS) at equilibrium, we notice that the conduction band consists essentially of Sn 5s and Sn 5p orbits while O 2s states have a low contribution. The upper valence bands are mainly construct from Sn 5p and O 2p states.



Fig. 3. Band structure and density of states for pure rutile-SnO<sub>2</sub> calculated using Tb-mBJ correction.



Fig. 4. Total and partial density of states for pure rutile-SnO<sub>2</sub> calculated using Tb-mBJ correction.

In table 2 we presented our calculated value of band gap within the LDA, and TB-mBJ correction compared with some experimental and theoretical values.

We notice that LDA underestimate energy gap value comparing to TB-mBJ result and to the experimental, other theoretical values.

	Ours LDA	TB-mBJ	Other theo.	Exp.	
Band gap energy Eg (eV)	1.077	3.142	0.832 - 2.760 - 1.38 - (Hassan et al., 2013; Li 2010; Gracia et al., 2007)	3.50 2.9 – 3.7 (Ferreir et al., Silva et al., 20 Baco et al., 2012)	a da 004;

## CONCLUSION

We have performed first-principles calculations to investigate the structural and electronic properties of  $SnO_2$  in the rutile-phase by the density functional theory based on full-potential linearized-augmented-plane wave's method (DFT/FP-LAPW) within the local density (LDA) approximation and TB-mBJ correction. The obtained values of the structural parameters such as lattice constants, bulk modulus and its pressure derivatives are in good agreement with experimental and other theoretical value.

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